Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs High-Performance Silicon-Gate CMOS

The MC74HCT374A may be used as a level converter for interfacing TTL or NMOS outputs to High–Speed CMOS inputs.

The HCT374A is identical in pinout to the LS374.

Data meeting the setup and hold time is clocked to the outputs with the rising edge of Clock. The Output Enable does not affect the state of the flip–flops, but when Output Enable is high, the outputs are forced to the high–impedance state. Thus, data may be stored even when the outputs are not enabled.

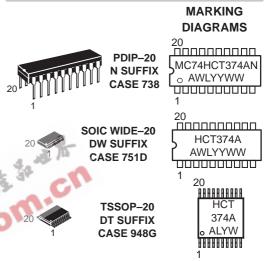
The HCT374A is identical in function to the HCT574A, which has the input pins on the opposite side of the package from the output pins. This device is similar in function to the HCT534A, which has inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS–Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 276 FETs or 69 Equivalent Gates
- Improvements over HCT374
 - Improved Propagation Delays
 - 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity



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A = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

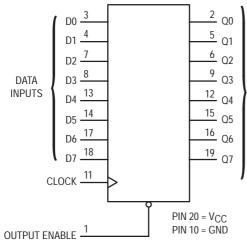
ORDERING INFORMATION

Device	Package	Shipping
MC74HCT374AN	PDIP-20	1440 / Box
MC74HCT374ADW	SOIC-WIDE	38 / Rail
MC74HCT374ADWR2	SOIC-WIDE	1000 / Reel
MC74HCT374ADT	TSSOP-20	75 / Rail
MC74HCT374ADTR2	TSSOP-20	2500 / Reel

NONINVERTING

OUTPUTS

LOGIC DIAGRAM



PIN ASSIGNMENT					
OUTPUT (1•	20	v _{cc}		
20 [2	19] Q7		
D0 [3	18] D7		
D1 [4	17] D6		
Q1 [5	16	D 06		
Q2 [6	15] Q5		
D2 [7	14	D5		
D3 [8	13] D4		
Q3 [9	12] Q4		
GND I	10	11	п сьоск		

FUNCTION TABLE

				Inputs		Output
V _{CC} GND			Output Enable	Clock	D	Q
		4	L L H		H L X	H L No Change Z
	18	E CC	X = don't Z = high i	care mpedanc	e	
lue	Units					
9)	ea.					

Design Criteria	Value	Units
Internal Gate Count*	69	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рJ

^{*}Equivalent to a two-input NAND gate.

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V
TA	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or V}_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or V}_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three–State Leakage Current	Output in High–Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	5.5	± 0.5	± 5.0	± 10	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND	5.5	4.0	40	160	μΑ

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

ΔlCC	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ –55 °C	25°C to 125°C	
	Candin	$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2.4	mA

NOTE: 1. Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

			Gu	aranteed Lin	nit	
Symbol	Parameter	•	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)		30	24	20	MHz
tPLH, tPHL	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)		31	39	47	ns
tPLZ, tPHZ	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)		30	38	45	ns
tPZL, tPZH	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)		30	38	45	ns
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 4)	_ 4	12	15	18	ns
C _{in}	Maximum Input Capacitance	九节	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	201	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Flip-Flop)*	65	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS ($V_{CC} = 5.0 \text{ V} \pm 10\%$, Input $t_f = t_f = 6.0 \text{ ns}$)

		Guaranteed Limit			
Symbol	Parameter	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Data to Clock (Figure 3)	12	15	18	ns
th	Minimum Hold Time, Clock to Data (Figure 3)	5.0	5.0	5.0	ns
t _W	Minimum Pulse Width, Clock (Figure 1)	12	15	18	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	500	500	500	ns

SWITCHING WAVEFORMS

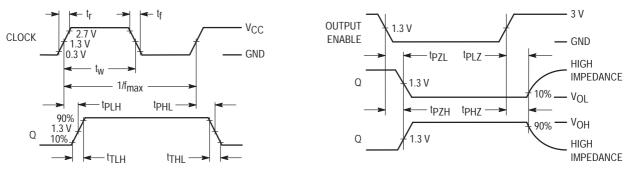
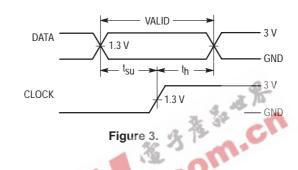
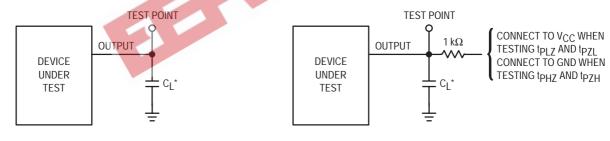


Figure 1.

Figure 2.



TEST CIRCUITS



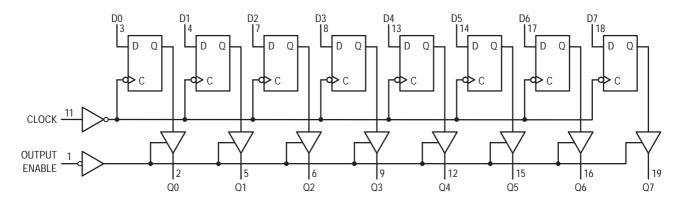
*Includes all probe and jig capacitance

*Includes all probe and jig capacitance

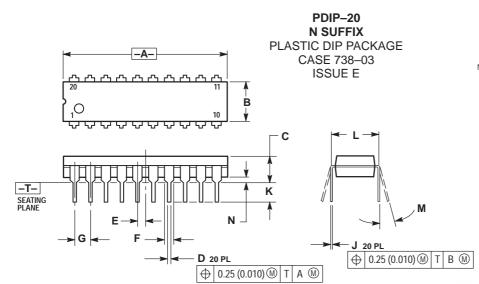
Figure 4.

Figure 5.

EXPANDED LOGIC DIAGRAM



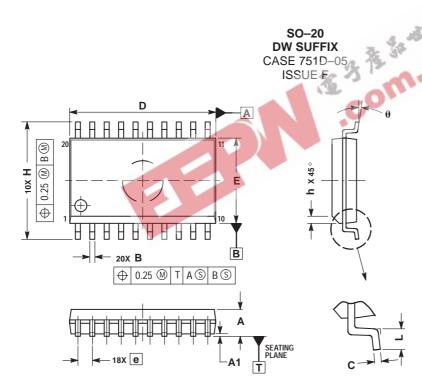
PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- TO DIMENSIONING AND TOLERANGING PER AL Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Ε	0.050	BSC	1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300	BSC	7.62	BSC	
M	0 °	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

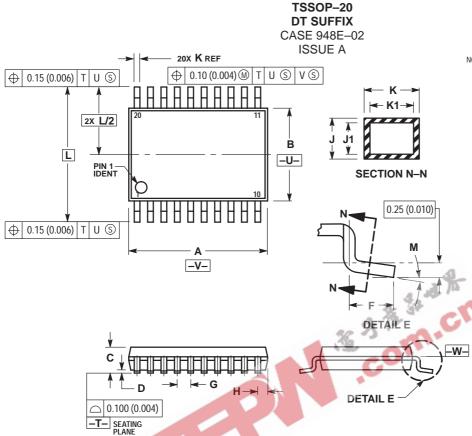


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 - DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL
 BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W...

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
M	0°	8°	0°	8°	



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